

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI THX15** is a Common Emitter Device Designed for High Linearity Class A/AB HF Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	10 A
V_{CB}	110 V
P_{DISS}	233 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
q_{JC}	0.75 °C/W

PACKAGE STYLE .550 4L STUD		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B		1.050/26,67
C	.545/13,84	.555/14,10
D	.495/12,57	.505/12,83
E	.003/0,08	.007/0,18
F		.830/21,08
G	.185/4,70	.198/5,03
H	.497/12,62	.530/13,46

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA	55			V
BV_{CES}	I _C = 100 mA V _{BE} = 0 V	110			V
BV_{CBO}	I _C = 100 mA	110			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _{CE} = 60 V V _{BE} = 0 V			5.0	mA
I_{CEO}	V _{CE} = 30 V			5.0	mA
h_{FE}	V _{CE} = 6.0 V I _C = 1.4 A	15		50	---
C_{ob}	V _{CB} = 50 V f = 1.0 MHz			220	pF
P_g	V _{CE} = 50 V I _{cq} = 100 mA	14			dB
IMD₃	f = 30 MHz P _{out} = 150 W (PEP)	37	-37	-30	dBc
h_c			45		%